

PNP SILICON EPITAXIAL TRANSISTOR 2SB1571

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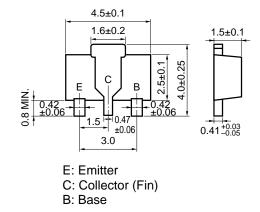
FEATURES

- Low VCE(sat): VCE(sat)1 ≤ −0.35 V
- Complementary to 2SD2402

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Collector to Base Voltage	Vсво	-50	V			
Collector to Emitter Voltage	VCEO	-30	V			
Emitter to Base Voltage	Vево	-6.0	V			
Collector Current (DC)	IC(DC)	-5.0	Α			
Collector Current (pulse) Note1	C(pulse)	-8.0	Α			
Base Current (DC)	B(DC)	-0.2	Α			
Base Current (pulse) Note1	B(pulse)	-0.4	Α			
Total Power Dissipation Note2	Pτ	2.0	W			
Junction Temperature	Tj	150	°C			
Storage Temperature Range	Tstg	–55 to + 150	°C			
Notes 1. PW \leq 10 ms, Duty Cycle \leq 50%						
2. When mounted on ceramic substrate of 16 cm ² x 0.7 mm						





ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

	-		1			
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	Ісво	Vcb = -50 V, IE = 0			-100	nA
Emitter Cut-off Current	Іево	VEB = -6.0 V, Ic = 0			-100	nA
DC Current Gain Note	hfe1	Vce = -1.0 V, Ic = -1.0 A	80			_
	hfe2	V _{CE} = -1.0 V, Ic = -2.0 A	100	200	400	_
Base to Emitter Voltage Note	VBE	Vce = -1.0 V, Ic = -0.1 A	-0.6	-0.665	-0.7	V
Collector Saturation Voltage Note	V _{CE(sat)1}	Ic = -3.0 A, Iв = -0.15 A		-0.17	-0.35	V
Collector Saturation Voltage Note	V _{CE(sat)2}	Ic = -5.0 A, Iв = -0.25 A		-0.28	-0.55	V
Base Saturation Voltage Note	V _{BE(sat)}	Ic = –3.0 А, Iв = –0.15 А		-0.89	-1.2	V
Gain Bandwidth Product	f⊤	Vce = -10 V, Ie = 0.5 A		150		MHz
Output Capacitance	Cob	Vсв = –10 V, IE = 0, f = 1.0 MHz		100		pF
Turn-on Time	ton	Ic = −2.0 A, Vcc = −10 V,		265		ns
Storage Time	tstg	R∟ = 5.0 Ω, Iв1 = −Iв2 = −0.1 A,		350		ns
Fall Time	tr			50		ns

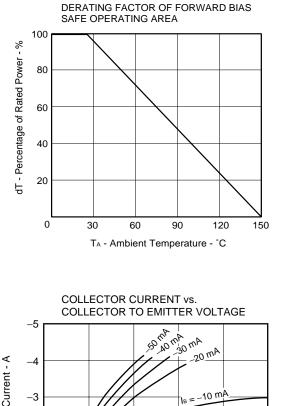
Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

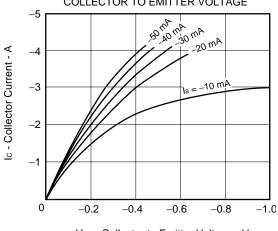
hFE CLASSFICATION

Marking	HX	HY	HZ
hFE2	100 to 200	160 to 320	200 to 400

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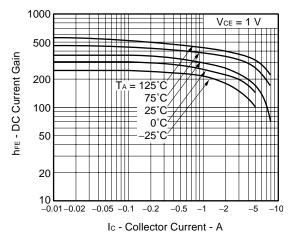
TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

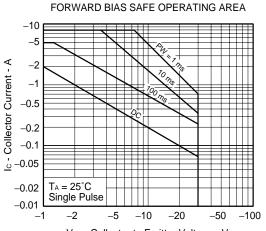




VcE - Collector to Emitter Voltage - V

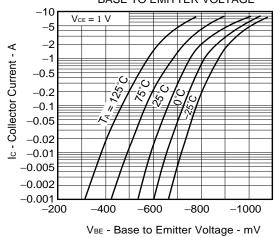
DC CURRENT GAIN vs. COLLECTOR CURRENT



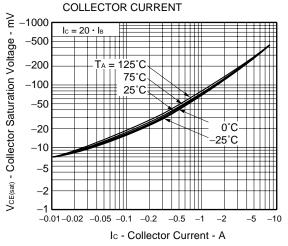


VCE - Collector to Emitter Voltage - V

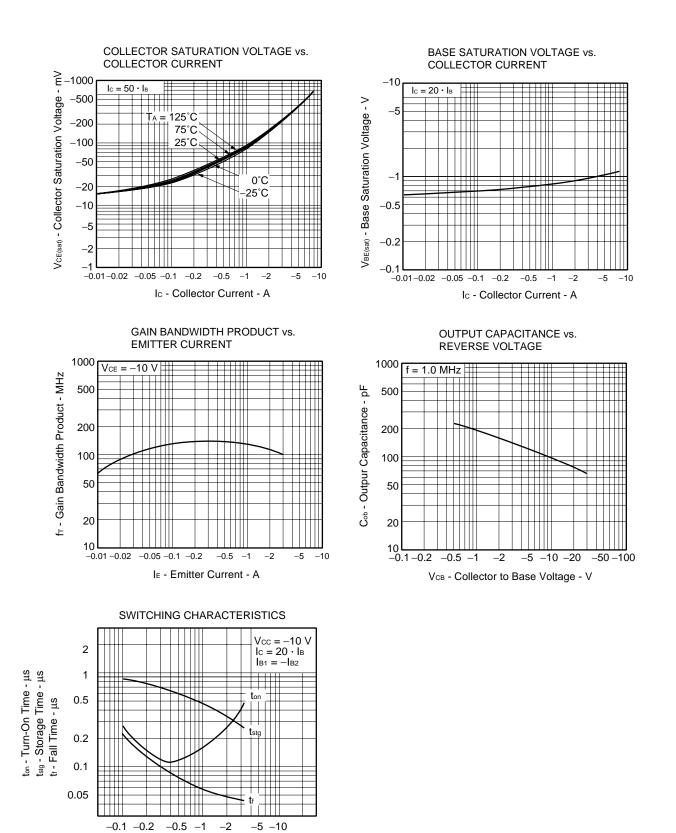
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR SATURATION VOLTAGE vs.



Data Sheet D15930EJ2V0DS



Ic - Collector Current - A

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